



IXFH170N25X3 Information

Heisener.com

Part Number IXFH170N25X3

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 250V 170A TO247

TO-247-3 **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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Certified Quality

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IXFH170N25X3 Specifications

Manufacturer Part Number IXFHI70N25X3 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 170A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 190nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 13500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3		
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-247 (IXFH) Package / Case MOSFET (Metal Oxide) MOSFET (Metal Oxide) 250V 250V 250V 170A (Tc) 170	Series	HiPerFET?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-247 (IXFH) Package / Case 170A (Tc)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 170A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 190nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 13500pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature **Operating Temperature** Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case **To-247-3	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id 4.5V @ 4mA Gate Charge (Qg) (Max) @ Vgs 190nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 13500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	170A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 13500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 13500pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case	Vgs(th) (Max) @ Id	4.5V @ 4mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)960W (Tc)Rds On (Max) @ Id, Vgs7.4 mOhm @ 85A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXFH)Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	190nC @ 10V
FET Feature - Power Dissipation (Max) 960W (Tc) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	13500pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.4 mOhm @ 85A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs7.4 mOhm @ 85A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247 (IXFH)Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Power Dissipation (Max)	960W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	7.4 mOhm @ 85A, 10V
Supplier Device Package TO-247 (IXFH) Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247 (IXFH)
Report errors?	Package / Case	TO-247-3
		Report errors?

IXFH170N25X3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFH170N25X3 Payment Methods



















IXFH170N25X3 Shipping Methods













If you have any question about IXFH170N25X3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com